



AMENDMENT TRANSMITTAL LETTER

Docket No.
M4065.0315/P315

Application No.
09/651,998

Filing Date
August 31, 2000

Examiner
H. Tsai

Art Unit
2812

Applicant(s): Er-Xuan Ping, et al.

Invention: METHOD AND STRUCTURE FOR REDUCING LEAKAGE CURRENT IN CAPACITORS

TO THE COMMISSIONER FOR PATENTS

Transmitted herewith is an amendment in the above-identified application.

The fee has been calculated and is transmitted as shown below.

CLAIMS AS AMENDED					
	Claims Remaining After Amendment	Highest Number Previously Paid	Number Extra Claims Present	Rate	
Total Claims	38	- 95 =	0	x	\$0.00
Independent Claims	5	- 7 =	0	x	\$0.00
Multiple Dependent Claims (check if applicable) <input type="checkbox"/>					
Other fee (please specify):					
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT:					\$0.00

☒ Large Entity

☐ Small Entity

☐ No additional fee is required for this amendment.

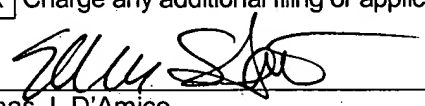
☒ Please charge Deposit Account No. 04-1073 in the amount of \$ \$290.00
A duplicate copy of this sheet is enclosed.

☐ A check in the amount of \$ _____ to cover the filing fee is enclosed.

☒ The Commissioner is hereby authorized to charge and credit Deposit Account No. 04-1073
as described below. A duplicate copy of this sheet is enclosed.

☐ Credit any overpayment.

☒ Charge any additional filing or application processing fees required under 37 CFR 1.16 and 1.17.


Thomas J. D'Amico
Attorney Reg. No. 28,371
Ellen S. Tao
Attorney Reg. No.: 43,383

Dated: April 30, 2002

DICKSTEIN SHAPIRO MORIN & OSHINSKY LLP
2101 L Street NW
Washington, DC 20037-1526
(202) 785-9700



Docket No.: M4065.0315 / P317dtb
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Er-Xuan Ping, et al.

Application No.: 09/651,998.

Group Art Unit: 2812

Filed: August 31, 2000

Examiner: H. Tsai

For: METHOD AND STRUCTURE FOR
REDUCING LEAKAGE CURRENT IN
CAPACITORS

**SECOND AMENDMENT UNDER 37 CFR 1.116
AND REQUEST FOR RECONSIDERATION**

* two identical
copies of claims,
no mark up
copy. HST *

Box AF
Commissioner for Patents
Washington, DC 20231

Dear Sir:

In response to the Office Action dated November 30, 2001 (Paper No. 9), finally rejecting claims 1-95, and pursuant to the Advisory Action mailed April 9, 2002, please amend the above-identified U.S. Patent application as follows:

In the Claims

Please cancel claims 2, 43, and 60-95 without prejudice.

1. (Amended) A method of forming a capacitor on a substrate in a semiconductor device, comprising:

forming a first layer of a conductive material over said substrate;

forming a second layer of a dielectric over said first layer, said second layer having a thickness not exceeding about 60 Angstroms;